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PATENT
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ABSTRACT OF THE DISCLOSURE

A method of fabricating a thin film transistor includes forming an amorphous silicon layer as an active layer on a substrate, forming a gate insulating layer and a gate electrode on the amorphous silicon layer, doping impurities of a first
5 conductive type in the amorphous silicon layer, forming a metal layer on the exposed portions of the amorphous silicon layer, and crystallizing the amorphous silicon layer by applying thermal treatment and electric field to the resultant substrate.

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